

Radiation Hardness of DOIM

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DOIM for Run2a

- Laser Diode type: InGaAsP/InP, $\lambda = 1550$ nm.
- Threshold current: 10 mA for each diode.
- Operating bias: 20 mA for each diode(Fig 1).
- Typical light output: 200 μ W to 800 μ W.
- Exposed to 200 kRad (400 kRad), no significant change in IV curve of LD (Fig 2).
- But light output degrade to 87% (80%) (Fig 3).
- Maximum radiation tolerance ~ 1 MRad(Fig 4).

New Technology

- VCSEL(Vertical Cavity Surface Emitting Lasers).
- Laser Diode type: GaAlAs, $\lambda = 850$ nm.
- Threshold current: 5 mA for each diode.
- Operating bias: 10 mA for each diode.
- Typical light output: 500 μ W to 3 mW.
- Exposed to 2.0×10^{14} proton/cm² (~ 40 MRad), light output degrade to 30% \sim 50% of the original level (Fig 5).
- For comparison, another 2.0×10^{14} proton/cm² were delivered to this VCSEL laser diode after being biased at 20 mA for 1 week. The annealing effect showed up at the beginning (Fig 6).
- Radiation tests for fiber, ASIC driver chip are in progress.

IV and LV Curves of LD for DOIM in Run 2a

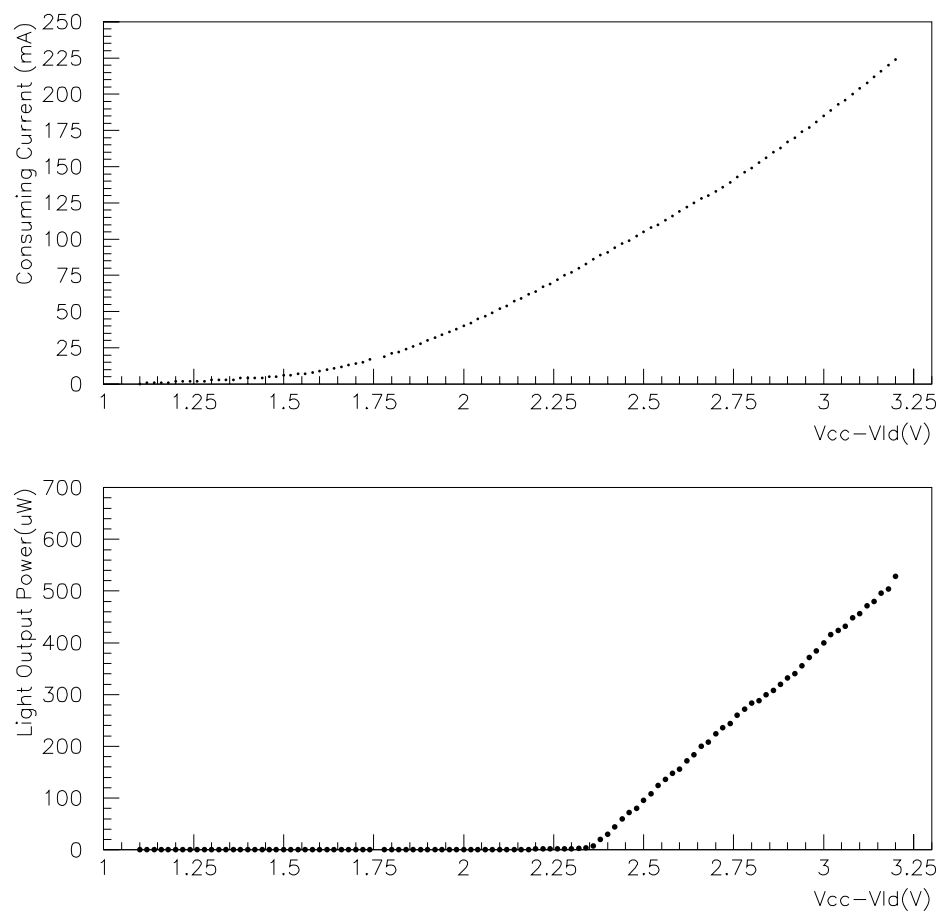


Figure 1:

No Significant Change in LV Curves

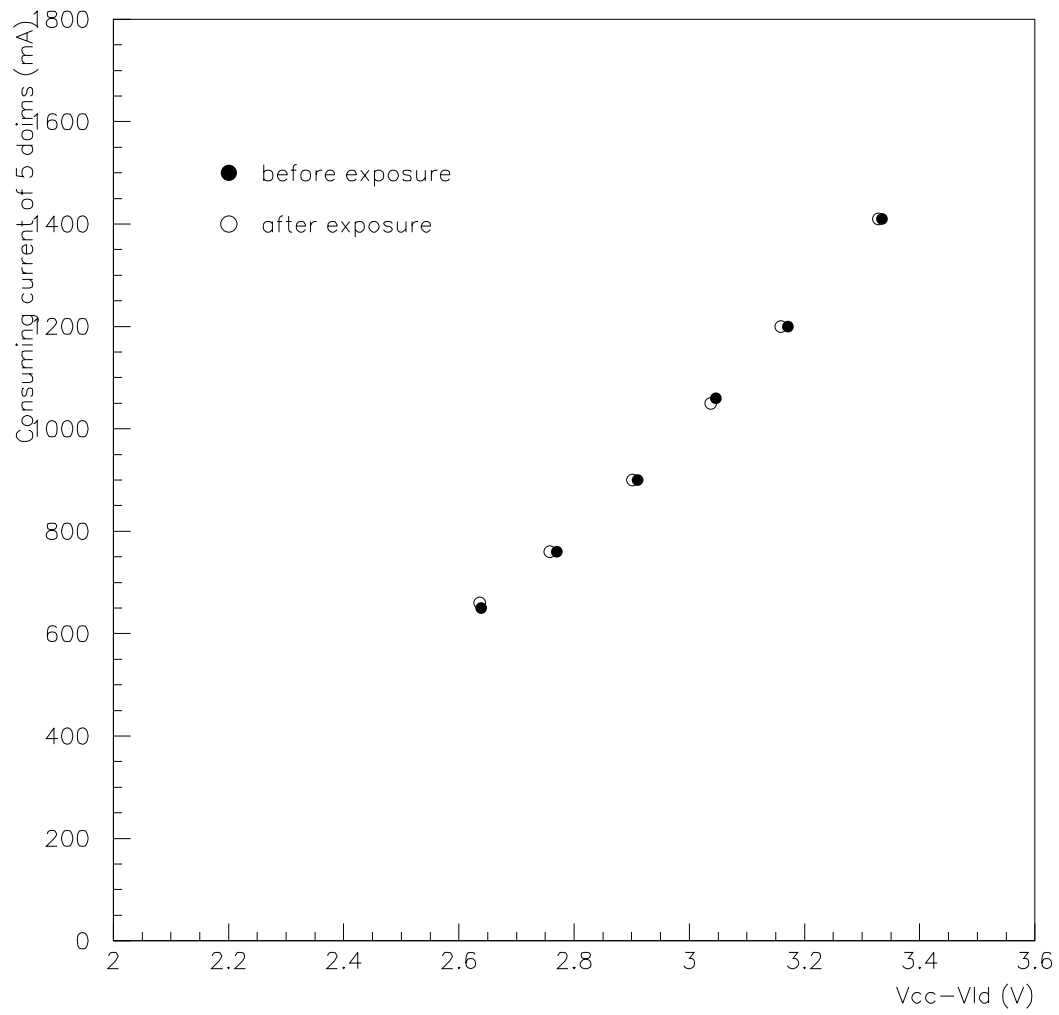


Figure 2:

Light Output Degrade

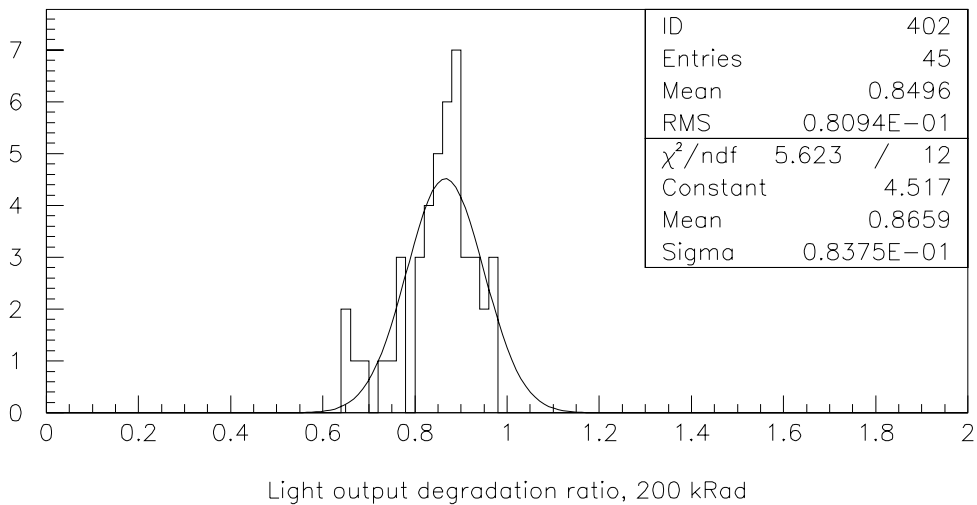
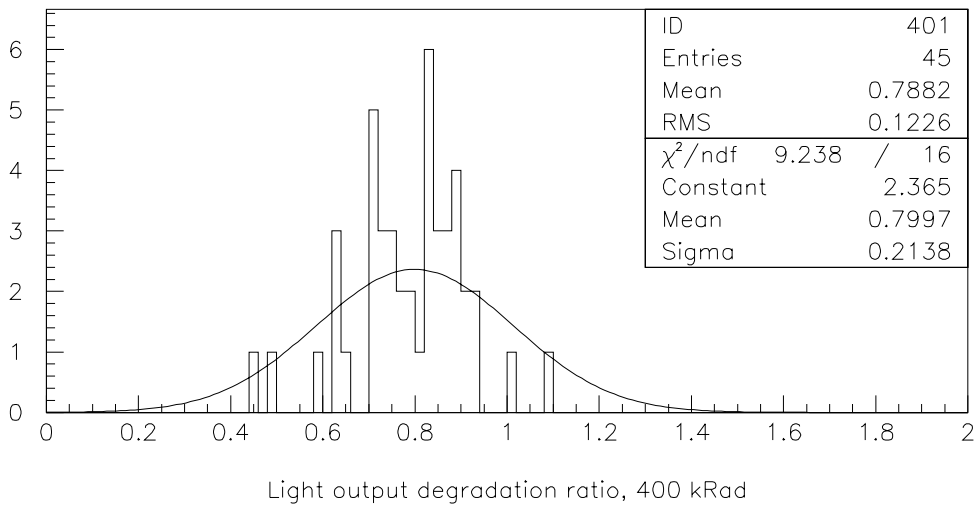


Figure 3:

DOIM TX MI8 Irradiation Test (Dec 10-14, 1997)

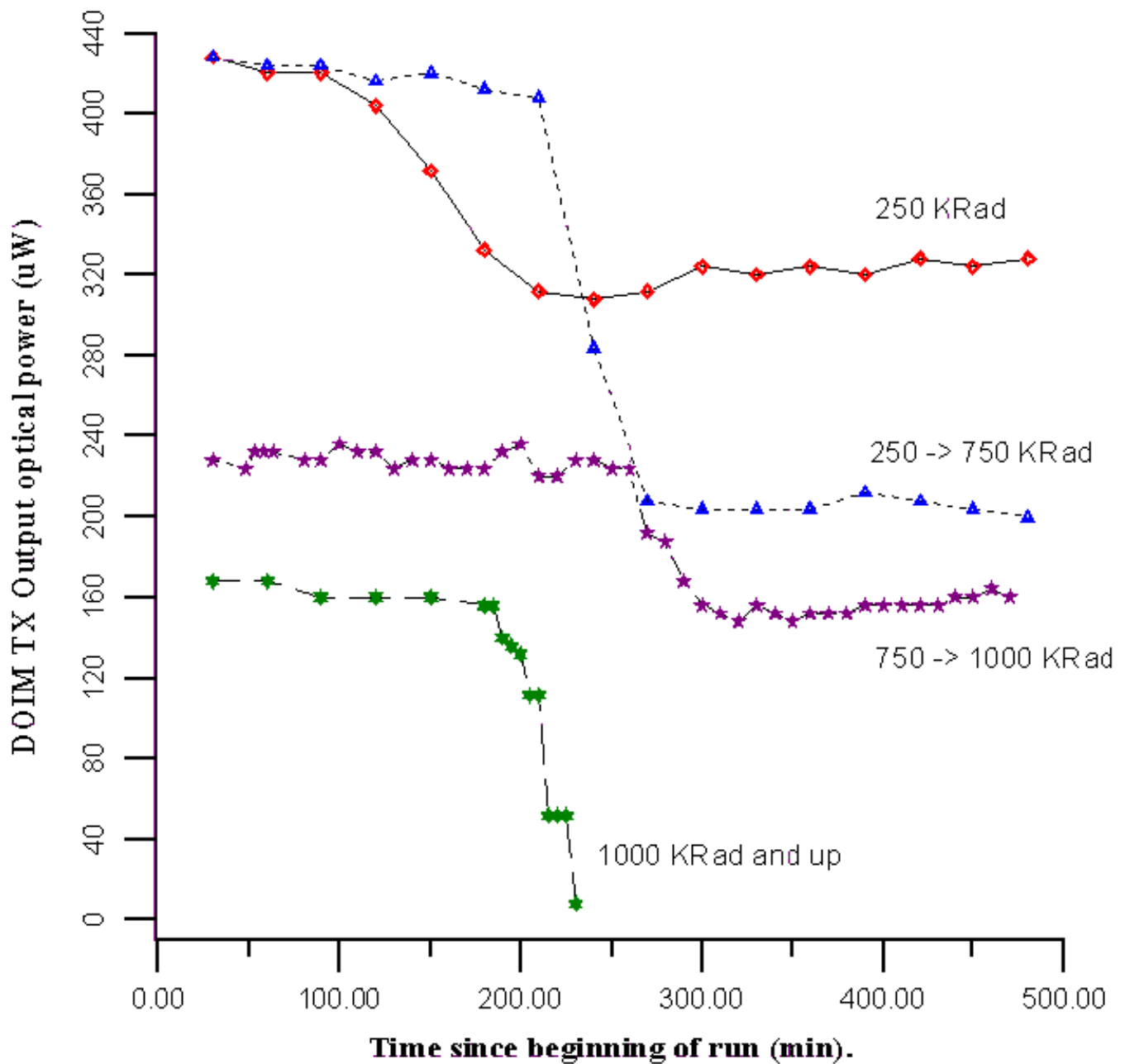


Figure 4:

TWN3 LD2

1st Irradiation

Total Fluence = 2.0E14 p/cm2

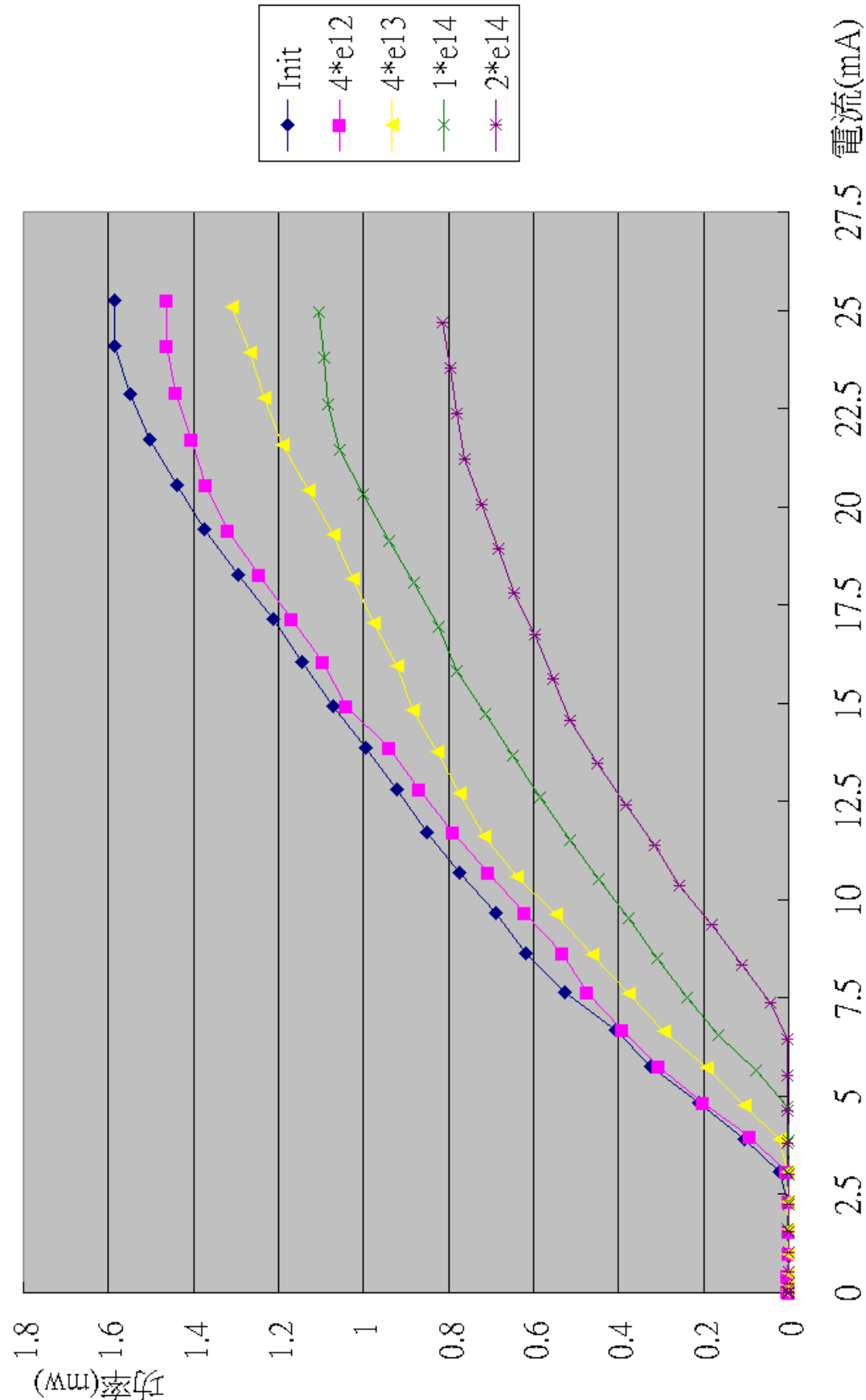


Figure 5:

TWN3 LD2
2nd irradiation
Total fluence = 4.0E14/cm2

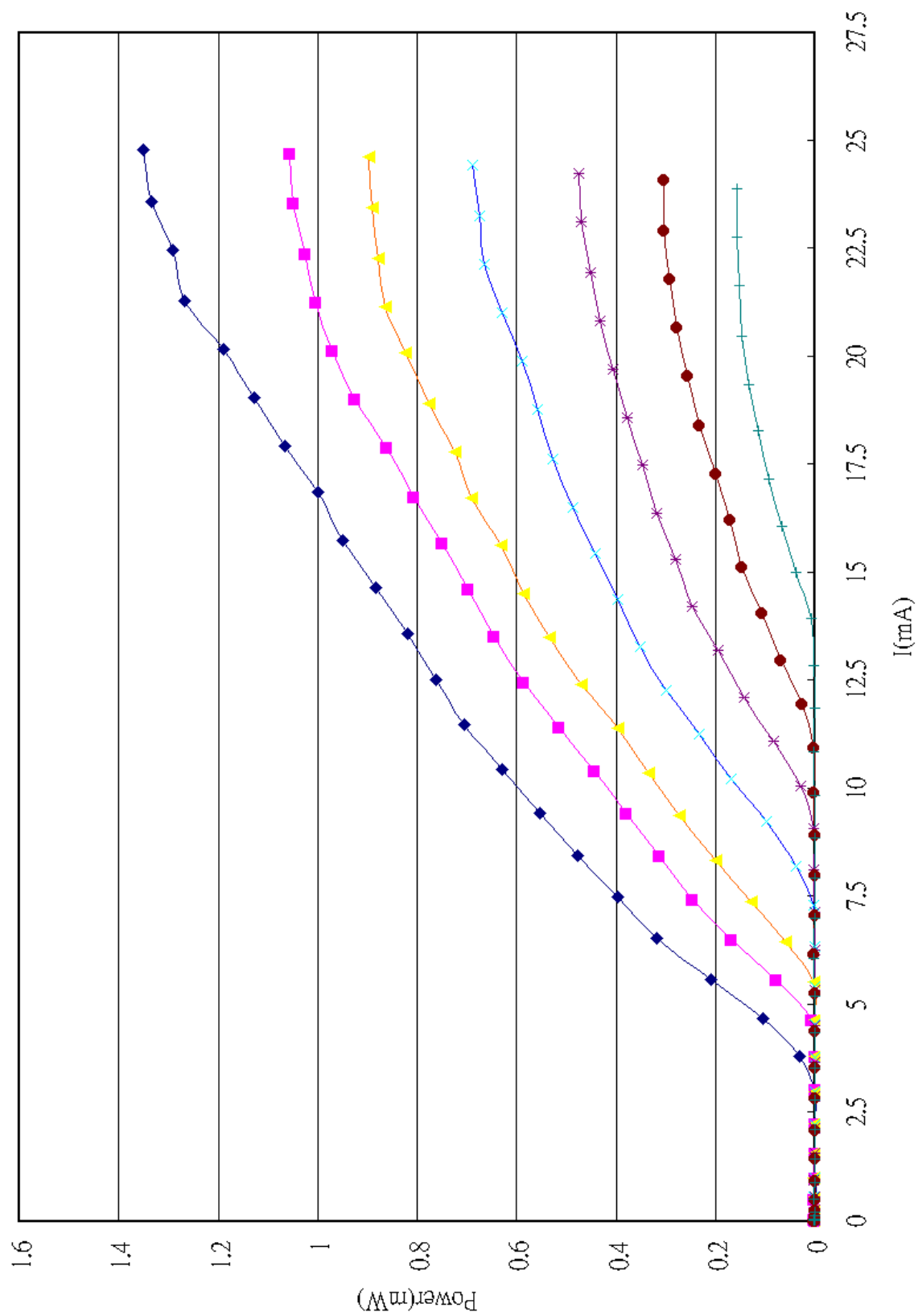


Figure 6: